

Isolated CAN Transceiver with Integrated High Voltage, Bus-Side, Linear Regulator

Preliminary Technical Data

ADM3052

FEATURES

Isolated CAN transceiver Integrated V+ linear regulator Bus side powered by V+ and V-11 V to 25 V operation on V+ 5 V or 3.3 V operation on V_{DD1} Complies with ISO 11898 Standard High speed data rates up to 1 Mbps **Short Circuit Protection on bus pins** Integrated bus mis-wire protection Unpowered nodes do not disturb the bus Connect 110 or more nodes on the bus Thermal shutdown protection High common-mode transient immunity: >25 kV/µs Safety and regulatory approvals (pending) UL recognition: 5000 V_{RMS} for 1 minute per UL 1577 **VDE Certificates of Conformity** DIN VVDE V 0884-10 (VDE V 0884-10):2006-12 VIORM = 848V peak

Industrial operating temperature range (-40°C to +85°C)

Available in wide-body, 16-lead SOIC package

APPLICATIONS

CAN data buses Industrial field networks DeviceNet applications

GENERAL DESCRIPTION

The ADM3052 is an isolated controller area network (CAN) physical layer transceiver with a $V_{\scriptscriptstyle +}$ integrated linear regulator. The ADM3052 complies with the ISO 11898 standard.

The device employs Analog Devices, Inc., iCoupler* technology to combine a 3-channel isolator, a CAN transceiver and an LDO regulator into a single package. The power is isolated between a single 3.3V or 5V supply on $V_{\rm DDI}$, the logic side, and a single 24V supply provided on V_+ , the bus side.

FUNCTIONAL BLOCK DIAGRAM

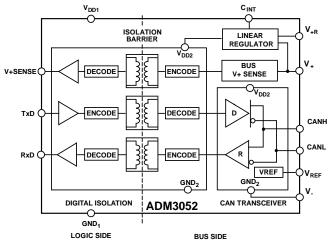


Figure 1.

The ADM3052 creates an isolated interface between the CAN protocol controller and the physical layer bus. It is capable of running at data-rates up to 1Mbps.

The device has integrated mis-wire protection on the bus pins, V+, V-, CANH and CANL.

The device has current-limiting and thermal shutdown features to protect against output short circuits and situations where the bus might be shorted to ground or power terminals. The part is fully specified over the industrial temperature range and is available in a 16-lead, wide-body SOIC package.

Rev. Pro

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ADM3052

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SPECIFICATIONS

All voltages are relative to their respective ground; $3.0 \text{ V} \leq V_{DD1} \leq 5.5 \text{ V}$. $T_A = -40^{\circ}\text{C}$ to $+85^{\circ}\text{C}$, $V_+ = 11 \text{ V}$ to 25 V, unless otherwise noted.

Table 1.

Parameter	Symbol	Min	Тур	Max	Unit	Test Conditions
SUPPLY CURRENT						
Power Supply Current Logic Side						
TxD/RxD Data Rate 1 Mbps	I _{DD1}		2.5		mA	
Power Supply Current Bus Side						
Recessive State	I ₊		10		mA	$R_L = 60 \Omega$, see Figure 10
Dominant State	I ₊		64		mA	$R_L = 60 \Omega$, see Figure 10
TxD/RxD Data Rate 1 Mbps	I+		48		mA	$R_L = 60 \Omega$, see Figure 10
EXTERNAL RESISTOR						
Resistance	R_P	297	300	303	Ω	
Power Rating			0.75		W	
DRIVER						
Logic Inputs						
Input Voltage High	VIH	0.7 V _{DD1}			V	TxD
Input Voltage Low	V _{IL}			$0.25 V_{DD1}$	V	TxD
CMOS Logic Input Currents	I _{IH} , I _{IL}			500	μΑ	TxD
Differential Outputs					'	
Recessive Bus Voltage	V _{CANL} , V _{CANH}	2.0		3.0	V	$V_{TxD} = 4 \text{ V}, R_L = \infty$, see Figure 7
CANH Output Voltage,	V _{CANH}	2.75		4.5	V	$V_{TxD} = 1 \text{ V, see Figure 7}$
CANL Output Voltage	V _{CANI}	0.5		2.0	V	$V_{TxD} = 1 \text{ V, see Figure 7}$
Differential Output Voltage	V _{OD}	1.5		3.0	V	$V_{TxD} = 1 \text{ V}, R_L = 45 \Omega, \text{ see Figure 7}$
. 3	V _{OD}	-500		+50	mV	$V_{TxD} = 4 \text{ V}, R_L = \infty$, see Figure 7
Short-Circuit Current, CANH	I _{SCCANH}			-200	mA	$V_{CANH} = -5 \text{ V}$
Short-Circuit Current, CANH	Isccanh		-100		mA	$V_{CANH} = -36 \text{ V}$
Short-Circuit Current, CANL	Isccanl			200	mA	$V_{CANL} = 36 \text{ V}$
RECEIVER						
Differential Inputs						
Differential Input Voltage Recessive	V_{IDR}	-1.0		+0.5	V	$-7 \text{ V} < V_{\text{CANL}}, V_{\text{CANH}} < 12 \text{ V},$
. 3						see Figure 8, C _L = 15 pF
Differential Input Voltage Dominant	V_{IDD}	0.9		5.0	V	-7 V < V _{CANL} , V _{CANH} <12 V,
						see Figure 8, C _L = 15 pF
Input Voltage Hysteresis	V _{HYS}		150		mV	See Figure 4.
CANH, CANL Input Resistance	R _{IN}	5		25	kΩ	
Differential Input Resistance	R _{DIFF}	20		100	kΩ	
Logic Outputs						
Output Low Voltage	V _{OL}		0.2	0.4	V	I _{оит} = 1.5 mA
Output High Voltage	V _{OH}	$V_{DD1} - 0.3$	$V_{\text{DD1}}-0.2$		V	$I_{OUT} = -1.5 \text{ mA}$
Short-Circuit Current	los	7		85	mA	$V_{OUT} = GND_1 \text{ or } V_{DD1}$
VOLTAGE REFERENCE						
Reference Output Voltage	V_{REF}	2.025		3.025	V	$ I_{REF} = 50 \mu\text{A} $
BUS VOLTAGE SENSE						
V₊Sense Output Voltage Low	V _{OL}		0.2	0.4	V	$I_{O+SENSE} = 1.5 \text{ mA}$
V₊Sense Output Voltage High	V _{он}	V _{DD1} - 0.3	V _{DD1} - 0.2		V	$I_{O+SENSE} = -1.5 \text{ mA}$
Bus Voltage Sense Threshold Voltage	V_{+TH}	7.5		10	V	
COMMON-MODE TRANSIENT IMMUNITY ¹		25			kV/μs	V _{CM} = 1 kV, transient
						magnitude = 800 V

¹ CM is the maximum common-mode voltage slew rate that can be sustained while maintaining specification-compliant operation. V_{CM} is the common-mode potential difference between the logic and bus sides. The transient magnitude is the range over which the common-mode is slewed. The common-mode voltage slew rates apply to both rising and falling common-mode voltage edges.

TIMING SPECIFICATIONS

All voltages are relative to their respective ground; $3.0 \text{ V} \leq V_{DD1} \leq 5.5 \text{ V}$. $T_A = -40^{\circ}\text{C}$ to $+85^{\circ}\text{C}$, $V_+ = 11 \text{ V}$ to 25 V, unless otherwise noted.

Table 2.

Parameter	Symbol	Min	Тур	Max	Unit	Test Conditions
DRIVER						
Maximum Data Rate		1			Mbps	
Propagation Delay from TxD On to Bus Active	t _{onTxD}			90	ns	See Figure 2 and Figure 9, $R_L = 60 \Omega$, $C_L = 100 \text{ pF}$
Propagation Delay from TxD Off to Bus Inactive	t _{offTxD}			120	ns	See Figure 2 and Figure 9, $R_L = 60 \Omega$, $C_L = 100 \text{ pF}$
RECEIVER						
Propagation Delay from TxD On to Receiver Active	t _{onRxD}			200	ns	See Figure 2 and Figure 9, $R_L = 60 \Omega$, $C_L = 100 \text{ pF}$
Propagation Delay from TxD Off to Receiver Inactive	t _{offRxD}			250	ns	See Figure 2 and Figure 9, $R_L = 60 \Omega$, $C_L = 100 \text{ pF}$
Bus Dominant to RxD Low	t _{dRxDL}			1	μs	See Figure 2 and Figure 9, $R_L = 60 \Omega$, $C_L = 100 \text{ pF}$
POWER UP						
Enable Time, V+ High to V+Sense Low	t _{SE}			300	μs	See Figure 5
Disable Time, V+ Low to V+Sense High	t _{SD}			10	ms	See Figure 5

SWITCHING CHARACTERISTICS

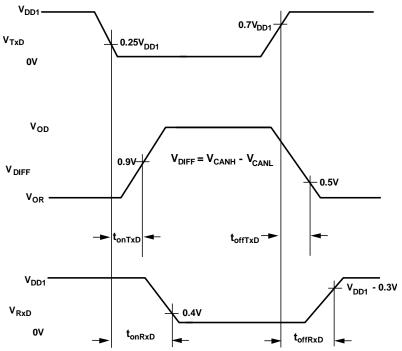


Figure 2. Driver and Receiver Propagation Delay

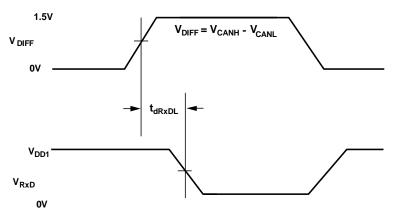


Figure 3. Bus Dominant to RxDL

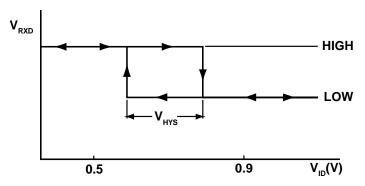
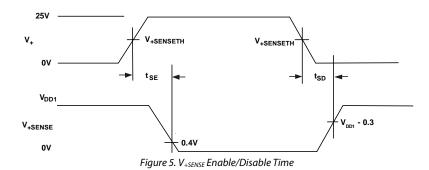


Figure 4. Receiver Input Hysteresis



ADM3052

REGULATORY INFORMATION

Table 3. Pending ADM3052 Approvals

Organization	Approval Type	Notes
UL	Recognized under the component recognition program of underwriters laboratories, Inc.	In accordance with UL 1577, each ADM3052 is proof tested by applying an insulation test voltage \geq 6000 V rms for 1 second (current leakage detection limit = 5 μ A)
VDE	Certified according to DIN V VDE V 0884-10 (VDE V 0884-10):2006-12	In accordance with DIN V VDE V 0884-10, each ADM3052 is proof tested by applying an insulation test voltage ≥1590 V peak for 1 second (partial discharge detection limit = 5 pC)

INSULATION AND SAFETY-RELATED SPECIFICATIONS

Table 4.

Parameter	Symbol	Value	Unit	Conditions
Rated Dielectric Insulation Voltage		5000	V rms	1-minute duration
Minimum External Air Gap (External Clearance)	L(I01)	7.7	mm	Measured from input terminals to output terminals, shortest distance through air
Minimum External Tracking (Creepage)	L(102)	7.6	mm	Measured from input terminals to output terminals, shortest distance along body
Minimum Internal Gap (Internal Clearance)		0.017 min	mm	Insulation distance through insulation
Tracking Resistance (Comparative Tracking Index)	CTI	>175	V	DIN IEC 112/VDE 0303-1
Isolation Group		Illa		Material group (DIN VDE 0110)

VDE 0884 INSULATION CHARACTERISTICS (PENDING)

This isolator is suitable for basic electrical isolation only within the safety limit data. Maintenance of the safety data must be ensured by means of protective circuits.

Table 5.

Description	Conditions	Symbol	Characteristic	Unit
CLASSIFICATIONS				
Installation Classification per DIN VDE 0110 for Rated				
Mains Voltage				
≤150 V rms			I to IV	
≤300 V rms			l to III	
≤400 V rms			l to II	
Climatic Classification			40/85/21	
Pollution Degree	DIN VDE 0110		2	
VOLTAGE				
Maximum Working Insulation Voltage		V _{IORM}	848	V peak
Input-to-Output Test Voltage		V_{PR}		
Method b1	$V_{IORM} \times 1.875 = V_{PR}$, 100% production tested, $t_m = 1$ sec, partial discharge < 5 pC		1590	V peak
Method a	3		1357	V peak
After Environmental Tests, Subgroup 1	$V_{IORM} \times 1.6 = V_{PR}$, $t_m = 60$ sec, partial discharge <5 pC			'
Method a			1018	V peak
After Input and/or Safety Test, Subgroup 2/3):	$V_{IORM} \times 1.2 = V_{PR}$, $t_m = 60$ sec, partial discharge <5 pC			·
Highest Allowable Overvoltage		V_{TR}	6000	V peak
SAFETY-LIMITING VALUES				
Case Temperature		Ts	150	°C
Input Current		I _{S, INPUT}	265	mA
Output Current		I _{S, OUTPUT}	335	mA
Insulation Resistance at Ts		Rs	>109	Ω

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ABSOLUTE MAXIMUM RATINGS

 $T_A = 25$ °C, unless otherwise noted. All voltages are relative to their respective ground.

Table 6.

ParameterRatingVDD1-0.5 V to +6 VV+-36 V to +36 VV+R-36 V to +36 VDigital Input Voltage TXD-0.5 V to VDD1 + 0.5 VDigital Output Voltage RXD-0.5 V to VDD1 + 0.5 VV+SENSE-0.5 V to VDD1 + 0.5 VCANH, CANL-36 V to +36 VOperating Temperature Range-40°C to +85°CStorage Temperature Range-55°C to +150°CESD (Human Body Model) on CANH, CANL, V+ and V - pinsTBDLead Temperature300°CVapor Phase (60 sec) Infrared (15 sec)215°CΘJA Thermal Impedance53°C/WTJ Junction Temperature130°C	Tuble 0.						
V _{+R} V _{+R} Digital Input Voltage TxD Digital Output Voltage RxD V _{+SENSE} CANH, CANL Operating Temperature Range Storage Temperature Range ESD (Human Body Model) on CANH, CANL, V+ and V- pins Lead Temperature Soldering (10 sec) Vapor Phase (60 sec) Infrared (15 sec) θ _{JA} Thermal Impedance -36 V to +36 V -0.5 V to V _{DD1} + 0.5 V -0.5 V to V	Parameter	Rating					
V _{+R} Digital Input Voltage TxD Digital Output Voltage RxD V _{+SENSE} CANH, CANL Operating Temperature Range Storage Temperature Range ESD (Human Body Model) on CANH, CANL, V+ and V- pins Lead Temperature Soldering (10 sec) Vapor Phase (60 sec) Infrared (15 sec) θ _{JA} Thermal Impedance -0.5 V to V _{DD1} + 0.5 V V To	V _{DD1}	−0.5 V to +6 V					
Digital Input Voltage TXD Digital Output Voltage RXD V+SENSE CANH, CANL Operating Temperature Range Storage Temperature Range ESD (Human Body Model) on CANH, CANL, V+ and V – pins Lead Temperature Soldering (10 sec) Vapor Phase (60 sec) Infrared (15 sec) θ _{JA} Thermal Impedance -0.5 V to V _{DD1} + 0.5 V -0.5 V to V _{DD1} + 0.5 V -0.5 V to V _{DD1} + 0.5 V To V _{DD1}	V_{+}	−36 V to +36 V					
TxD Digital Output Voltage RxD V+SENSE CANH, CANL Operating Temperature Range Storage Temperature Range ESD (Human Body Model) on CANH, CANL, V+ and V – pins Lead Temperature Soldering (10 sec) Vapor Phase (60 sec) Infrared (15 sec) θ _{JA} Thermal Impedance -0.5 V to V _{DD1} + 0.5 V -0.5 V to V _{DD1} + 0.5 V -0.5 V to V _{DD1} + 0.5 V To V _{DD1} +	V_{+R}	−36 V to +36 V					
Digital Output Voltage RxD V+SENSE CANH, CANL Operating Temperature Range Storage Temperature Range ESD (Human Body Model) on CANH, CANL, V+ and V – pins Lead Temperature Soldering (10 sec) Vapor Phase (60 sec) Infrared (15 sec) θJA Thermal Impedance O-55 V to V _{DD1} + 0.5 V -0.5 V to V _{DD1} + 0.5 V -36 V to +36 V -40°C to +85°C -55°C to +150°C TBD 300°C 215°C 220°C 53°C/W	Digital Input Voltage						
RxD V+SENSE CANH, CANL Operating Temperature Range Storage Temperature Range ESD (Human Body Model) on CANH, CANL, V+ and V- pins Lead Temperature Soldering (10 sec) Vapor Phase (60 sec) Infrared (15 sec) θ _{JA} Thermal Impedance O.5 V to V _{DD1} + 0.5 V -0.5 V to V _{DD1} + 0.5 V -36 V to +36 V -40°C to +85°C -55°C to +150°C TBD TBD 300°C 215°C 220°C 53°C/W	TxD	$-0.5 \text{ V to V}_{DD1} + 0.5 \text{ V}$					
V _{+SENSE} CANH, CANL Operating Temperature Range Storage Temperature Range ESD (Human Body Model) on CANH, CANL, V+ and V- pins Lead Temperature Soldering (10 sec) Vapor Phase (60 sec) Infrared (15 sec) θ _{JA} Thermal Impedance -0.5 V to V _{DD1} + 0.5 V -36 V to +36 V -40°C to +85°C -55°C to +150°C TBD 300°C 215°C 220°C 53°C/W	Digital Output Voltage						
CANH, CANL Operating Temperature Range Storage Temperature Range ESD (Human Body Model) on CANH, CANL, V+ and V- pins Lead Temperature Soldering (10 sec) Vapor Phase (60 sec) Infrared (15 sec) θ _{JA} Thermal Impedance -36 V to +36 V -40°C to +85°C TBD TBD 300°C 215°C 220°C 53°C/W	RxD	$-0.5 \text{ V to V}_{DD1} + 0.5 \text{ V}$					
Operating Temperature Range Storage Temperature Range ESD (Human Body Model) on CANH, CANL, V+ and V – pins Lead Temperature Soldering (10 sec) Vapor Phase (60 sec) Infrared (15 sec) θ _{JA} Thermal Impedance -40°C to +85°C -55°C to +150°C TBD 300°C 220°C 220°C 53°C/W	V_{+SENSE}	$-0.5 \text{ V to V}_{DD1} + 0.5 \text{ V}$					
Storage Temperature Range ESD (Human Body Model) on CANH, CANL, V+ and V – pins Lead Temperature Soldering (10 sec) Vapor Phase (60 sec) Infrared (15 sec) 9JA Thermal Impedance -55°C to +150°C TBD 300°C 2215°C 220°C 53°C/W	CANH, CANL	−36 V to +36 V					
ESD (Human Body Model) on CANH, CANL, V+ and V- pins Lead Temperature Soldering (10 sec) Vapor Phase (60 sec) Infrared (15 sec) θ _{JA} Thermal Impedance TBD 300°C 215°C 220°C 53°C/W	Operating Temperature Range	−40°C to +85°C					
CANL, V+ and V – pins Lead Temperature Soldering (10 sec) Vapor Phase (60 sec) Infrared (15 sec) θ _{JA} Thermal Impedance SANCH STATE OF THE S	Storage Temperature Range	−55°C to +150°C					
Lead Temperature300°CSoldering (10 sec)300°CVapor Phase (60 sec)215°CInfrared (15 sec)220°Cθ _{JA} Thermal Impedance53°C/W	ESD (Human Body Model) on CANH,	TBD					
Soldering (10 sec) 300°C Vapor Phase (60 sec) 215°C Infrared (15 sec) 220°C θ _{JA} Thermal Impedance 53°C/W	CANL, V+ and V– pins						
Vapor Phase (60 sec)215°CInfrared (15 sec)220°C $θ_{JA}$ Thermal Impedance53°C/W	Lead Temperature						
Infrared (15 sec) 220°C θ _{JA} Thermal Impedance 53°C/W	Soldering (10 sec)	300°C					
θ _{JA} Thermal Impedance 53°C/W	Vapor Phase (60 sec)	215℃					
12. 1 P 11. 11.	Infrared (15 sec)	220°C					
T _J Junction Temperature 130°C	θ_{JA} Thermal Impedance	53°C/W					
•	T _J Junction Temperature	130℃					

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ESD CAUTION



ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

PIN CONFIGURATION AND FUNCTION DESCRIPTIONS

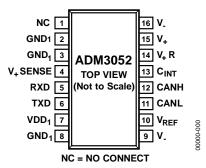


Figure 6. Pin Configuration

Table 7. Pin Function Descriptions

Pin No.	Mnemonic	Description
1	NC	No Connect.
2	GND ₁	Ground, Logic Side.
3	GND ₁	Ground, Logic Side.
4	V ₊ SENSE	Bus Voltage Sense. A High Level on V_{+SENSE} indicates that there is Power connected on the bus on V_{+} and V_{-} . A Low Level on V_{+SENSE} indicates that Power is not connected on the bus on V_{+} and V_{-} .
5	RXD	Receiver Output Data.
6	TXD	Driver Input Data.
7	V_{DD1}	Power Supply Logic side. Decoupling capacitor to GND $_1$ required; capacitor value should be between 0.01 μ F and 0.1 μ F.
8	GND ₁	Ground, Logic Side.
9	V_{-}	Ground, Bus Side.
10	V_{REF}	Reference voltage output.
11	CANL	Low-Level CAN Voltage Input/Output.
12	CANH	High-Level CAN Voltage Input/Output.
13	CINT	A capacitor of 1 μ F, 10 V is required on this pin.
14	V_{+R}	Connect a 300 Ω , 750 mW resistor between V ₊ R and V ₊ .
15	V_{+}	Bus Power Connection. Connect a 300 Ω , 750 mW resistor between V_+R and V_+ .
16	V_{-}	Ground, Bus Side.

TEST CIRCUITS

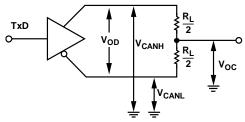


Figure 7. Driver Voltage Measurement

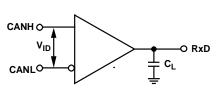


Figure 8. Receiver Voltage Measurements

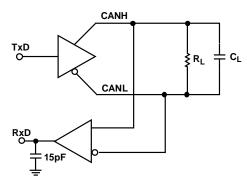


Figure 9. Switching Characteristics Measurements

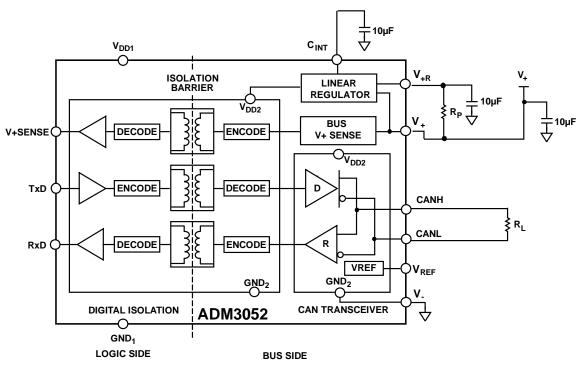


Figure 10. Supply Current Measurement Test Circuit

CIRCUIT DESCRIPTION

ELECTRICAL ISOLATION

In the ADM3052, electrical isolation is implemented on the logic side of the interface. Therefore, the part has two main sections: a digital isolation section and a transceiver section (see Figure 11). The driver input signal, which is applied to the TxD pin and referenced to the logic ground (GND₁), is coupled across an isolation barrier to appear at the transceiver section referenced to the isolated ground (V₋). Similarly, the receiver input and V+SENSE, which is referenced to the isolated ground in the transceiver section, is coupled across the isolation barrier to appear at the RxD pin and V+SENSE referenced to the logic ground respectively.

iCoupler Technology

The digital signals transmit across the isolation barrier using iCoupler technology. This technique uses chip scale transformer windings to couple the digital signals magnetically from one side of the barrier to the other. Digital inputs are encoded into waveforms that are capable of exciting the primary transformer winding. At the secondary winding, the induced waveforms are decoded into the binary value that was originally transmitted.

Positive and negative logic transitions at the input cause narrow (\sim 1 ns) pulses to be sent to the decoder via the transformer. The decoder is bistable and is, therefore, set or reset by the pulses, indicating input logic transitions. In the absence of logic transitions at the input for more than \sim 1 µs, a periodic set of refresh pulses, indicative of the correct input state, are sent to ensure dc correctness at the output. If the decoder receives no internal pulses for more than about 5 µs, then the input side is assumed to be unpowered or nonfunctional, in which case the output is forced to a default state (see Table 9).

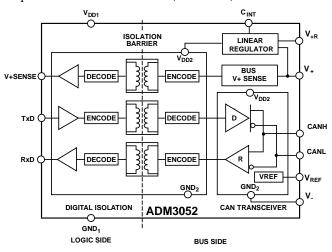


Figure 11. Digital Isolation and Transceiver Sections

TRUTH TABLES

The truth tables in this section use the abbreviations shown in Table 8.

Table 8. Truth Table Abbreviations

Letter	Description
Н	High level
L	Low level
1	Indeterminate
Χ	Don't Care
Z	High impedance (off)
NC	Disconnected

Table 9. Transmitting

Supply Status		Input	Outputs				
V_{DD1}	V ₊	TxD	Bus State	CANH	CANL	V+Sense	
On	On	L	Dominant	Н	L	L	
On	On	Н	Recessive	Z	Z	L	
On	On	Floating	Recessive	Z	Z	L	
Off	On	Χ	Recessive	Z	Z	1	
On	Off	L	1	1	1	Н	

Table 10. Receiving

Supply Status		Inputs	Outputs		
V _{DD1}	V+	V _{ID} = CANH – CANL	RxD	V+Sense	
On	On	≥ 0.9V	Dominant	L	L
On	On	≤ 0.5V	Recessive	Н	L
On	On	$0.5V < V_{ID} < 0.9V$	1	1	L
On	On	Inputs open	Recessive	Н	L
Off	On	Х	X	1	1
On	Off	Х	Χ	Н	Н

THERMAL SHUTDOWN

The ADM3052 contains thermal shutdown circuitry that protects the part from excessive power dissipation during fault conditions. Shorting the driver outputs to a low impedance source can result in high driver currents. The thermal sensing circuitry detects the increase in die temperature under this condition and disables the driver outputs. This circuitry is designed to disable the driver outputs when a junction temperature of 150°C is reached. As the device cools, the drivers re-enable at a temperature of 140°C.

LINEAR REGULATOR

The linear regulator takes the V+ bus power (ranging between 11V and 25V) and regulates this voltage to 5V, to provide power to the internal bus-side circuitry (iCoupler isolation, V+sense and transceiver circuits). The linear regulator uses two regulation loops to share the power dissipation between the internal die and an external resistor. This reduces the internal heat dissipation in the package. The 300Ω external resistor should be capable of dissipating 750 mW of power and have a tolerance of 1%.

MAGNETIC FIELD IMMUNITY

The limitation on the magnetic field immunity of the *i*Coupler is set by the condition in which an induced voltage in the receiving coil of the transformer is large enough to either falsely set or reset the decoder. The following analysis defines the conditions under which this may occur. The 3 V operating condition of the ADM3052 is examined because it represents the most susceptible mode of operation.

The pulses at the transformer output have an amplitude greater than 1 V. The decoder has a sensing threshold of about 0.5 V, thus establishing a 0.5 V margin in which induced voltages can be tolerated.

The voltage induced across the receiving coil is given by

$$V = \left(\frac{-d\beta}{dt}\right) \sum \pi r_n^2 \; ; \; n = 1, 2, \dots, N$$

where:

 β is the magnetic flux density (gauss). N is the number of turns in the receiving coil. r_n is the radius of the n^{th} turn in the receiving coil (cm).

Given the geometry of the receiving coil and an imposed requirement that the induced voltage is, at most, 50% of the 0.5 V margin at the decoder, a maximum allowable magnetic field can be determined using Figure 12.

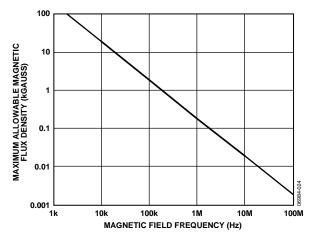


Figure 12. Maximum Allowable External Magnetic Flux Density

For example, at a magnetic field frequency of 1 MHz, the maximum allowable magnetic field of 0.2 kgauss induces a voltage of 0.25 V at the receiving coil. This is about 50% of the sensing threshold and does not cause a faulty output transition. Similarly, if such an event occurs during a transmitted pulse and is the worst-case polarity, it reduces the received pulse from >1.0 V to 0.75 V, still well above the 0.5 V sensing threshold of the decoder.

Figure 13 shows the magnetic flux density values in terms of more familiar quantities, such as maximum allowable current flow at given distances away from the ADM3052 transformers.

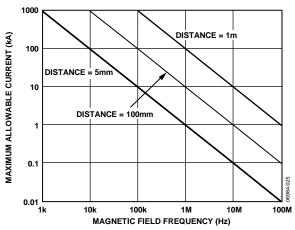


Figure 13. Maximum Allowable Current for Various Current-to-ADM3052 Spacings

With combinations of strong magnetic field and high frequency, any loops formed by PCB traces can induce error voltages large enough to trigger the thresholds of succeeding circuitry. Care should be taken in the layout of such traces to avoid this possibility.

APPLICATIONS INFORMATION

TYPICAL APPLICATIONS

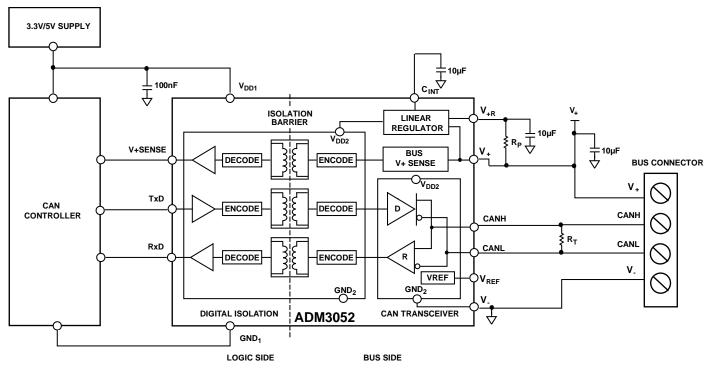
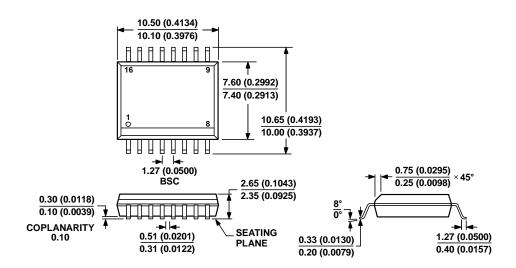


Figure 14. Typical Isolated CAN Node using the ADM3052

OUTLINE DIMENSIONS



COMPLIANT TO JEDEC STANDARDS MS-013-AA
CONTROLLING DIMENSIONS ARE IN MILLIMETERS; INCH DIMENSIONS
(IN PARENTHESES) ARE ROUNDED-OFF MILLIMETER EQUIVALENTS FOR
REFERENCE ONLY AND ARE NOT APPROPRIATE FOR USE IN DESIGN.

Figure 15. 16-Lead Standard Small Outline Package [SOIC_W]
Wide Body
(RW-16)
Dimensions shown in millimeters and (inches)

ORDERING GUIDE

Model ¹	Temperature Range	Package Description	Package Option
ADM3052BRWZ	−40°C to +85°C	16-Lead SOIC_W	RW-16
ADM3052BRWZ-REEL7	−40°C to +85°C	16-Lead SOIC_W	RW-16

 $^{^{1}}$ Z = RoHS Compliant Part.

NOTES

Preliminary Technical Data

ADM3052

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